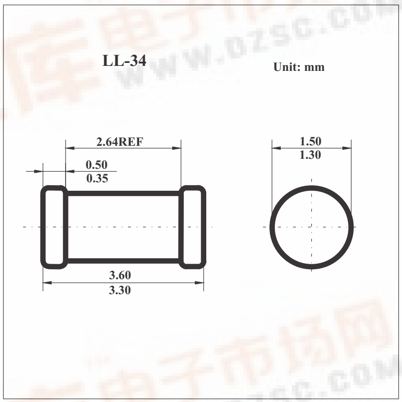
High Voltage,General Purpose Diode

KAV103(BAV103）



Features

- Silicon Epitaxial Planar Diodes
- For general purpose

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Working Inverse Voltage	Wiv	200	V
Average Rectified Current	I_O	200	mA
DC Forward Current	I_F	500	mA
Recurrent Peak Forward Current	if	600	mA
Peak Forward Surge Current　Pulse Width = 1.0 second	$i_{F(surge)}$	1	A
Pulse Width = 1.0 microsecond		4	
Total Power Dissipation at TA = 25℃	P_D	500	mW
Linear Derating Factor from TA = 25℃		3.33	mW/℃
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	350	℃/W
Operating Junction Temperature	T_J	-65 to +200	℃
Storage Temperature	T_{stg}	-65 to +200	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Breakdown Voltage	B_V	I_R = 100 uA	250			V
Reverse Leakage	I_R	V_R = 200 V			100	nA
		V_R = 200 V T_A = 150℃			100	uA
Forward Voltage	V_F	I_F = 100 mA			1.00	V
		I_F = 200 mA			1.25	V
Capacitance	C_T	V_R = 0.0 V,f = 1.0 MHz			5.0	pF
Reverse Recovery Time	T_{RR}	I_F= I_R =30 mA ,I_{RR}= 1.0 mA,R_L = 100Ω			50	ns